

Dmitry Yurasov

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50
papers

206
citations

8
h-index

12
g-index

53
ext. papers

237
ext. citations

1
avg, IF

2.54
L-index

#	Paper	IF	Citations
50	Antimony segregation in Ge and formation of n-type selectively doped Ge films in molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2015 , 118, 145701	2.5	19
49	Impact of growth and annealing conditions on the parameters of Ge/Si(001) relaxed layers grown by molecular beam epitaxy. <i>Semiconductors</i> , 2015 , 49, 1415-1420	0.7	18
48	Optical monitoring of technological parameters during molecular-beam epitaxy. <i>Semiconductors</i> , 2012 , 46, 1471-1475	0.7	18
47	Critical thickness for the Stranski-Krastanov transition treated with the effect of segregation. <i>Semiconductors</i> , 2008 , 42, 563-570	0.7	15
46	Recovery of SIMS depth profiles with account for nonstationary effects. <i>Applied Surface Science</i> , 2014 , 307, 33-41	6.7	13
45	Light emission from Ge(Si)/SOI self-assembled nanoislands embedded in photonic crystal slabs of various periods with and without cavities. <i>Semiconductor Science and Technology</i> , 2019 , 34, 024003	1.8	12
44	TOF-SIMS 5 instrument sensitivity to matrix elements in GeSi Layers: Analysis based on recording of complex secondary ions. <i>Journal of Surface Investigation</i> , 2011 , 5, 591-594	0.5	9
43	Secondary cluster ions Ge ₂ ⁺ and Ge ₃ ⁺ for improving depth resolution of SIMS depth profiling of GeSi/Si heterostructures. <i>Semiconductors</i> , 2010 , 44, 401-404	0.7	9
42	A new approach to the diagnostics of nanoislands in Ge _x Si _{1-x} /Si heterostructures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , 2014 , 40, 601-605	0.7	7
41	Selective etching of Si, SiGe, Ge and its usage for increasing the efficiency of silicon solar cells. <i>Semiconductors</i> , 2017 , 51, 1542-1546	0.7	7
40	Barrier-height modification in Schottky silicon diodes with highly doped 3D and 2D layers. <i>Semiconductors</i> , 2012 , 46, 1358-1361	0.7	6
39	Influence of elastic strains in sublayers on the critical thickness of the Stranski-Krastanow transition for the GeSi/Si(001) system. <i>Journal of Surface Investigation</i> , 2009 , 3, 548-553	0.5	6
38	Influence of thermal annealing on the electrical and luminescent properties of heavily Sb-doped Ge/Si(001) layers. <i>Semiconductor Science and Technology</i> , 2018 , 33, 124019	1.8	6
37	On the stimulated emission of InGaAs/GaAs/AlGaAs laser structures grown by MOCVD on exact and inclined Ge/Si(001) substrates. <i>Semiconductors</i> , 2017 , 51, 663-666	0.7	5
36	Quantitative calibration and germanium SIMS depth profiling in Ge _x Si _{1-x} /Si heterostructures. <i>Semiconductors</i> , 2014 , 48, 1109-1117	0.7	5
35	Method for taking into account the shift parameter in the deconvolution of the depth composition distribution of semiconductor structures from SIMS depth profiles. <i>Semiconductors</i> , 2012 , 46, 1481-1486	0.7	5
34	Transition from planar to island growth mode in SiGe structures fabricated on SiGe/Si(001) strain-relaxed buffers. <i>Applied Physics Letters</i> , 2012 , 101, 151601	3.4	5

33	Technology of the production of laser diodes based on GaAs/InGaAs/AlGaAs structures grown on a Ge/Si substrate. <i>Semiconductors</i> , 2017 , 51, 1477-1480	0.7	4
32	Influence of Annealing on the Properties of Ge:Sb/Si(001) Layers with an Antimony Concentration Above Its Equilibrium Solubility in Germanium. <i>Semiconductors</i> , 2019 , 53, 882-886	0.7	3
31	Use of related parameters in X-ray diffraction analysis of multilayer structures with allowance for the layer growth time. <i>Technical Physics</i> , 2014 , 59, 402-406	0.5	3
30	Transition from the two- to three-dimensional growth of Ge films upon deposition onto relaxed SiGe/Si(001) buffer layers. <i>Semiconductors</i> , 2013 , 47, 427-432	0.7	3
29	Growth of light-emitting SiGe heterostructures on strained silicon-on-insulator substrates with a thin oxide layer. <i>Semiconductors</i> , 2015 , 49, 1104-1110	0.7	3
28	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. <i>Semiconductors</i> , 2018 , 52, 1547-1550	0.7	3
27	Spin pump induced inverse spin Hall effect observed in Bi-doped n-type Si. <i>Physical Review B</i> , 2020 , 101,	3.3	2
26	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. <i>Technical Physics Letters</i> , 2015 , 41, 648-650	0.7	2
25	New approach to the X-ray diffraction analysis of test structures during flow calibration in epitaxial growth reactors. <i>Journal of Surface Investigation</i> , 2012 , 6, 494-497	0.5	2
24	Layer-by-layer analysis of structures containing δ layers by secondary ion mass spectrometry taking into account the TOF.SIMS-5 depth resolution function. <i>Journal of Surface Investigation</i> , 2012 , 6, 574-577 ^{0.5}	0.5	2
23	Direct comparison of superlattice periods measured with X-ray diffractometry and optical interferometry. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2011 , 75, 40-43	0.4	2
22	Study of the transition of the epitaxial Ge film from layer-to-layer to three-dimensional growth in heterostructures with strained SiGe sublayers. <i>Semiconductors</i> , 2010 , 44, 519-524	0.7	2
21	Nonlinear calibration curves in secondary ion mass spectrometry for quantitative analysis of GeSi heterostructures with nanoclusters. <i>Technical Physics Letters</i> , 2016 , 42, 243-247	0.7	2
20	Formation and Properties of Locally Tensile Strained Ge Microstructures for Silicon Photonics. <i>Semiconductors</i> , 2018 , 52, 1442-1447	0.7	2
19	Comparative Analysis of the Luminescence of Ge:Sb Layers Grown on Ge(001) and Si(001) Substrates. <i>Semiconductors</i> , 2019 , 53, 1318-1323	0.7	1
18	Locally Strained Ge/SOI Structures with an Improved Heat Sink as an Active Medium for Silicon Optoelectronics. <i>Semiconductors</i> , 2019 , 53, 1324-1328	0.7	1
17	Antimony segregation in stressed SiGe heterostructures grown by molecular beam epitaxy. <i>Semiconductors</i> , 2013 , 47, 1481-1484	0.7	1
16	Method of selective doping of silicon by segregating impurities. <i>Technical Physics Letters</i> , 2011 , 37, 824-826		1

15	Influence of surface roughness on a change in the growth mode from two-dimensional to three-dimensional for strained SiGe heterostructures. <i>Semiconductors</i> , 2016 , 50, 1630-1634	0.7	1
14	A New Limitation of the Depth Resolution in TOF-SIMS Elemental Profiling: the Influence of a Probing Ion Beam. <i>Technical Physics Letters</i> , 2018 , 44, 320-323	0.7	1
13	Influence of the Growth Conditions and Doping Level on the Luminescence Kinetics of Ge:Sb Layers Grown on Silicon. <i>Semiconductors</i> , 2020 , 54, 811-816	0.7	0
12	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , 2020 , 127, 165701	2.5	0
11	Influence of irradiation by Swift Heavy Ions (SHI) on electronic magnetotransport in Sb layer in silicon. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2022 , 138, 115047	3	0
10	Enhancement of the Luminescence Signal from Self-Assembled Ge(Si) Nanoislands due to Interaction with the Modes of Two-Dimensional Photonic Crystals. <i>Semiconductors</i> , 2020 , 54, 975-981	0.7	0
9	Plastic relaxation in GeSi layers on Si (001) and Si (115) substrates. <i>Semiconductors</i> , 2015 , 49, 19-22	0.7	
8	Hodographs in diode-structure diagnostics. <i>Semiconductors</i> , 2015 , 49, 1443-1447	0.7	
7	Electroluminescence of structures with self-assembled Ge(Si) nanoislands confined between strained Si layers. <i>Semiconductors</i> , 2016 , 50, 1657-1661	0.7	
6	On the radiative recombination and tunneling of charge carriers in SiGe/Si heterostructures with double quantum wells. <i>Semiconductors</i> , 2016 , 50, 1604-1608	0.7	
5	Antimony segregation in Si layers grown by molecular beam epitaxy on Si wafers with different crystallographic orientations. <i>Semiconductors</i> , 2017 , 51, 1552-1556	0.7	
4	Formation and Optical Properties of Locally Strained Ge Microstructures Embedded into Cavities. <i>Semiconductors</i> , 2021 , 55, 531	0.7	
3	Stimulated Emission in the 1.3-1.5 μm Spectral Range from AlGaInAs Quantum Wells in Hybrid Light-Emitting III-V Heterostructures on Silicon Substrates. <i>Semiconductors</i> , 2018 , 52, 1495-1499	0.7	
2	Stimulated Emission at 1.3- μm Wavelength in Metamorphic InGaAs/InGaAsP Structure with Quantum Wells Grown on Ge/Si(001) Substrate. <i>Technical Physics Letters</i> , 2018 , 44, 735-738	0.7	
1	Comparison of III-V Heterostructures Grown on Ge/Si, Ge/SOI, and GaAs. <i>Semiconductors</i> , 1	0.7	